Abstracts

S-Band GaAs Power FET

H.M. Macksey, H.Q. Tserng and G.H. Westphal. "S-Band GaAs Power FET." 1982 MTT-S International Microwave Symposium Digest 82.1 (1982 [MWSYM]): 150-152.

The design, fabrication, and performance of an S-band GaAs power FET are described. A pulsed 38.4 mm gate width device has produced up to 20 W with 8 dB gain across the 3 to 3.5 GHz band.

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